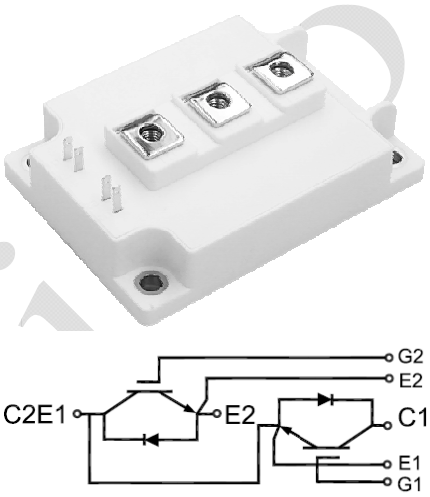
GTS600HF120A4H

IGBT Module

Preliminary Data

Features:

- Field Stop Trench Gate IGBT
- Low Saturation Voltage
- Low Switching Loss
- Short Circuit Rated ＞10μs
- 100% RBSOA Tested（2×Ic）
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



Applications:

- UPS
- SMPS
- Welding Machine
- Cutting Machine
- Induction Heating

IGBT, Inverter

Maximum Rated Values(T_C=25℃ unless otherwise specified)

V_{CES}	Collector-Emitter Blocking Voltage		1200	V
V_{GES}	Gate-Emitter Voltage		±20	V
I_C	Continuous Collector Current	T_C=100℃	600	A
		T_C=25℃	960	A
I_{CM}	Peak Collector Current Repetitive	T_J=175℃	1200	A
t_{SC}	Short Circuit Withstand Time		>10	μs
P_D	Maximum Power Dissipation (IGBT)	T_C=25℃ T_{Jmax}=175℃	3330	W

Electrical Characteristics of IGBT (T_C=25℃ unless otherwise specified)

Static Characteristics

Symbol	Description	Conditions		Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	I_C=12 mA, V_{CE}=V_{GE}		5.0	5.5	6.5	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C=600A, V_{GE}=15V	T_J=25℃		1.70	2.00	V
			T_J=125℃		2.10		V
I_{CES}	Collector-Emitter Leakage Current	V_{GE}=0V, V_{CE}=V_{CES}, T_J=25℃				1	mA
I_{GES}	Gate-Emitter Leakage Current	V_{GE}= ±20V, V_{CE}=0V, T_J=25℃				800	nA
C_{ies}	Input Capacitance	V_{CE}=25V, V_{GE}=0V , f =1MHz			61.6		nF
C_{res}	Reveres Transfer Capacitance				2.86		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	V_{CC}=600V,I_C=600A, R_{Gon} =1 Ω,V_{GE}=±15V, Inductive Load	T_J=25℃		812		ns
			T_J=125℃		838		
t_r	Rise Time		T_J=25℃		223		ns
			T_J=125℃		229		
$t_{d(off)}$	Turn-off Delay Time	V_{CC}=600V,I_C =600A, R_{Goff} =1 Ω,V_{GE}=±15V, Inductive Load	T_J =25℃		715		ns
			T_J =125℃		772		
t_f	Fall Time		T_J=25℃		148		ns
			T_J=125℃		165		
E_{on}	Turn-on Switching Loss	V_{CC}=600V,I_C=600A, R_{Gon}=1 Ω,V_{GE}= ±15V, Inductive Load di/dt =2192A/μs(T_J=125℃)	T_J=25℃		38.6		mJ
			T_J=125℃		50		
E_{off}	Turn-off Switching Loss	V_{CC}=600V,I_C=600A, R_{Goff} = 1 Ω,V_{GE}=±15V, Inductive Load du/dt =4141V/μs(T_J=125℃)	T_J=25℃		63.8		mJ
			T_J=125℃		76		
Q_g	Total Gate Charge	V_{GE}=-15V…+15V			5.95		μC
RBSOA	I_C=1200A,V_{CC}=1050V,Vp=1200V, R_{Goff}=1Ω, V_{GE}=+15V to 0V, T_J =150°C			Trapezoid			
SCSOA	V_{CC} = 300V, V_{GE} = 15V, T_J = 150℃			10			μs
$R_{\theta JC}$	IGBT Thermal Resistance: Junction-To-Case(per leg)				0.045		℃/W

Diode, Inverter

Maximum Rated Values (T_C=25℃ unless otherwise specified)

V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	600	A
I_{FM}	Peak FWD Current Repetitive	1200	A

Electrical Characteristics of FWD (T_C=25℃ unless otherwise specified)

V_{FM}	Forward Voltage	I_F=600A	T_J=25℃		1.70		V
			T_J=125℃		1.80		
t_{rr}	Reverse Recovery Time	I_F=600A, -di$_F$/dt=2672A/μs(T_J=125℃), V_R=600V, V_{GE}= -15V	T_J=25℃		301		ns
			T_J=125℃		440		
I_{rr}	Peak Reverse Recovery Current		T_J=25℃		319		A
			T_J=125℃		394		
Q_{rr}	Reverse Recovery Charge		T_J==25℃		59.8		μC
			T_J=125℃		99.1		
E_{rec}	Reverse Recovery Energy		T_J=25℃		27.5		mJ
			T_J=125℃		47.1		
$R_{\theta JC}$	Diode Thermal Resistance: Junction-To-Case(per leg)				0.068		℃/W

Module

Symbol	Description		Min	Typ	Max	Unit
V_{iso}	Isolation Voltage (All Terminals Shorted)	f = 50Hz, 1minute	2500			V
T_J	Maximum Junction Temperature				175	℃
T_{JOP}	Maximum Operating Junction Temperature Range		-40		+150	℃
T_{stg}	Storage Temperature		-40		+125	℃
CTI	Comparative Tracking Index		200			V
$R_{\theta CS}$	Case-To-Sink Thermally (Conductive Grease Applied)			0.01		℃/W
M	Power Terminals Screw:M6		3.5		5.0	N·m
M	Mounting Screw:M6		4.5		6.0	N·m
G	Weight			410		g

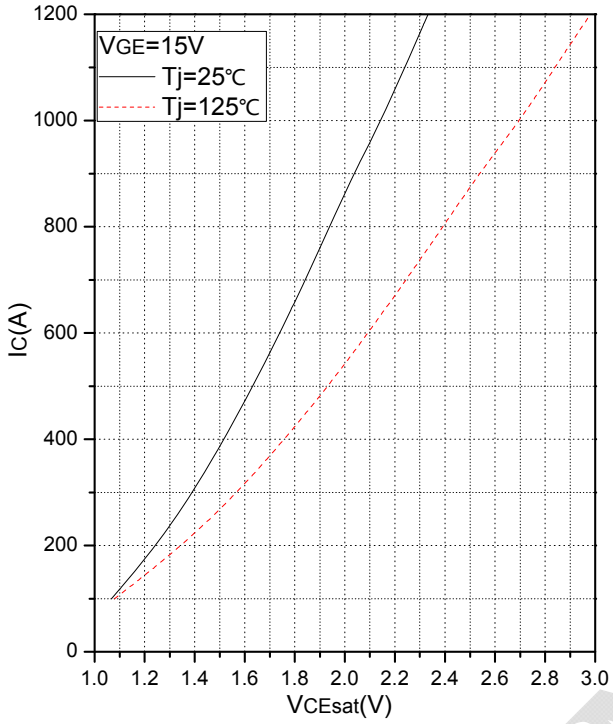


Fig.1 Typical Saturation Voltage Characteristics

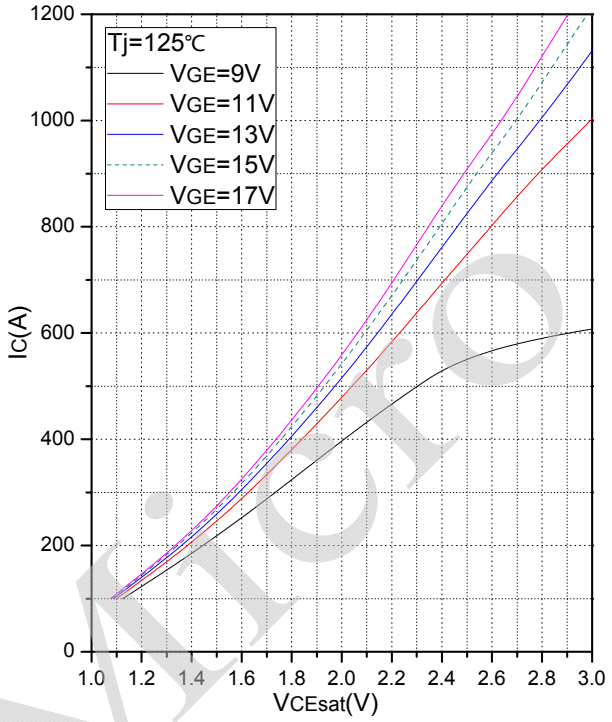


Fig.2 Typical Output Characteristics

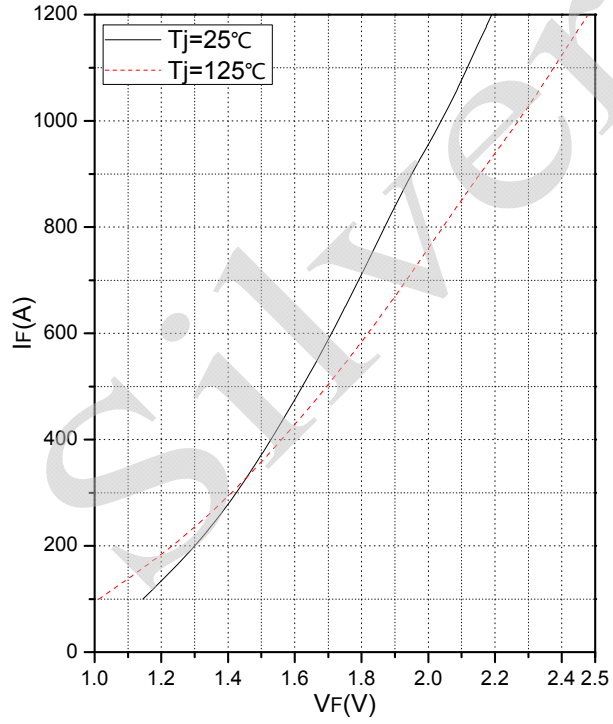


Fig.3 Forward Characteristics of FWD

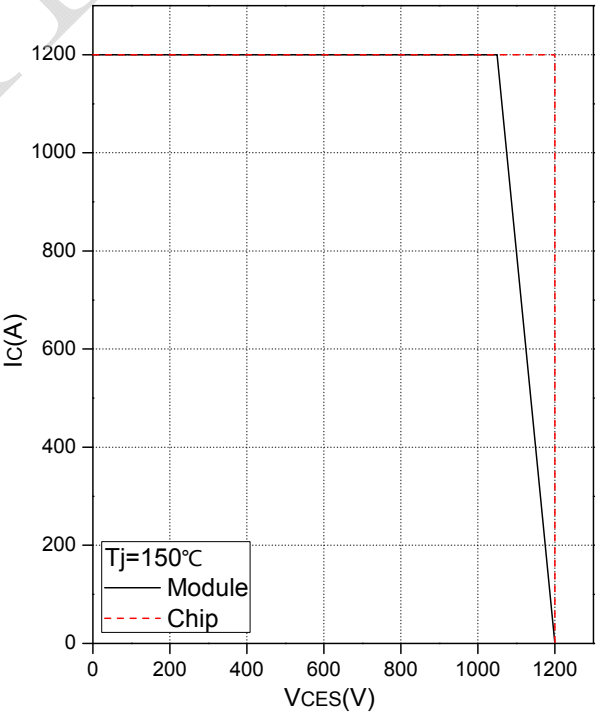


Fig.4 Reverse Bias Safe Operation Area (RBSOA)

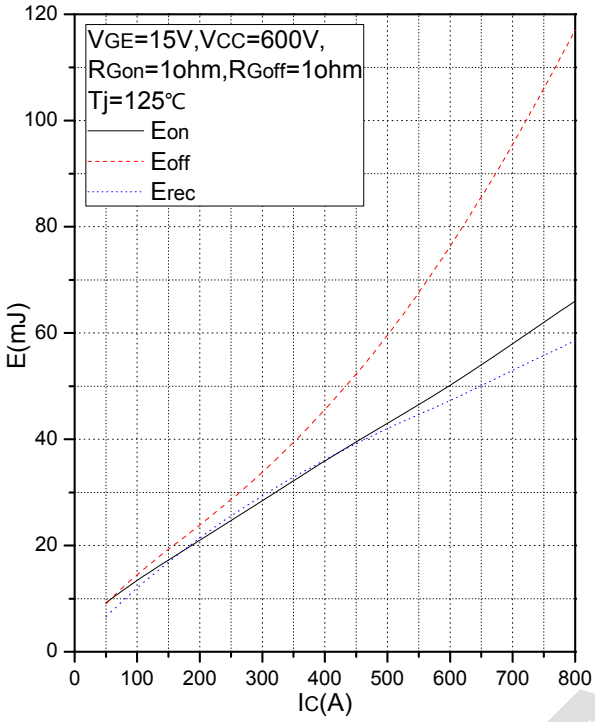


Fig.5 Typical Switching Loss vs. Collector Current

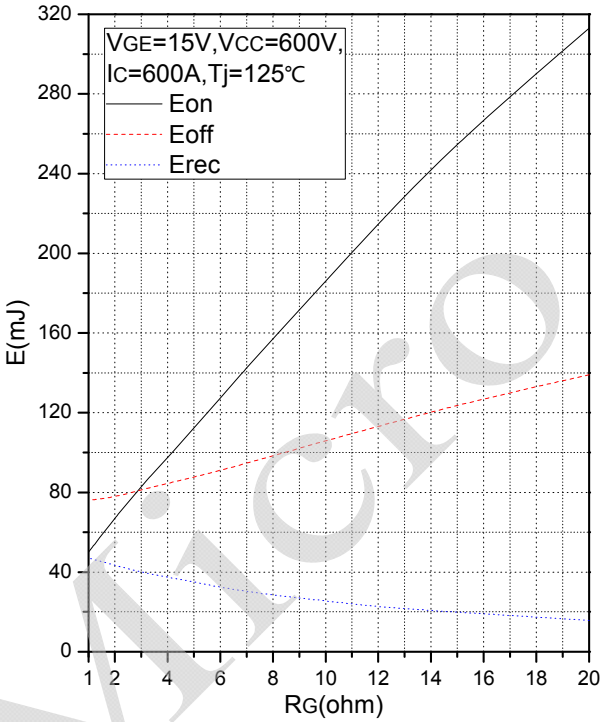


Fig.6 Typical Switching Loss vs. Gate Resistance

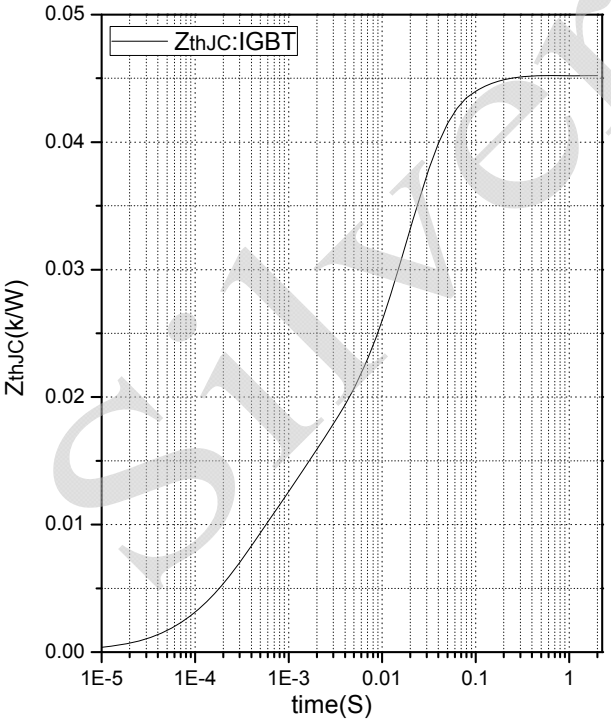


Fig.7 Transient Thermal Impedance (IGBT)

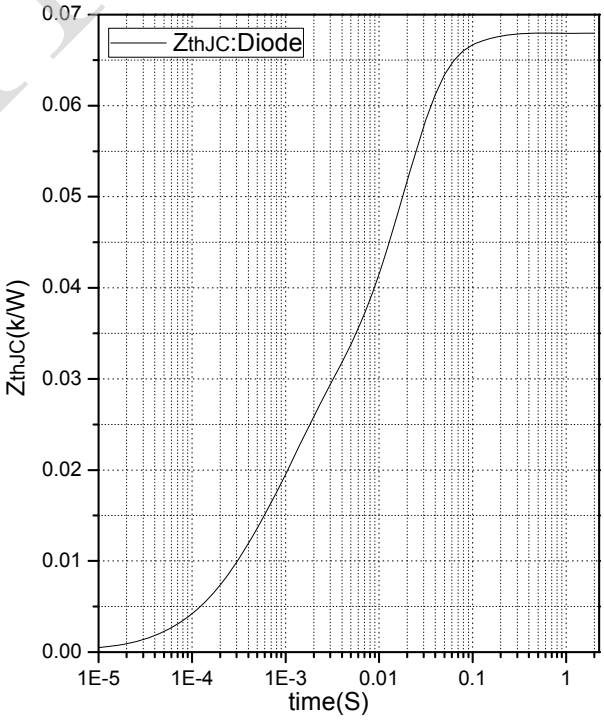
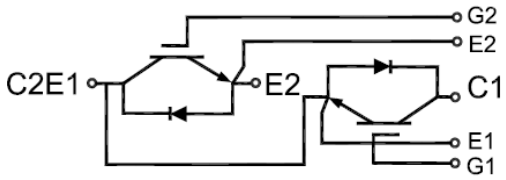
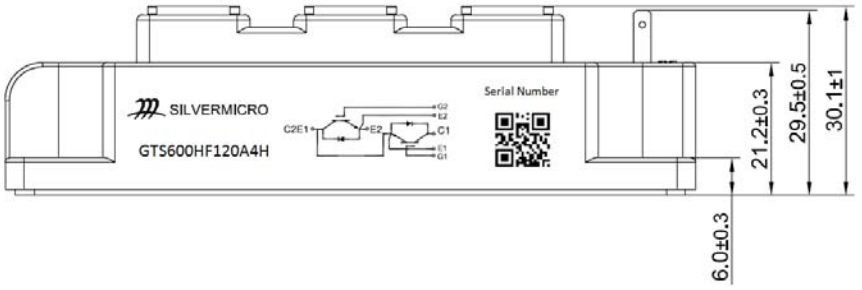


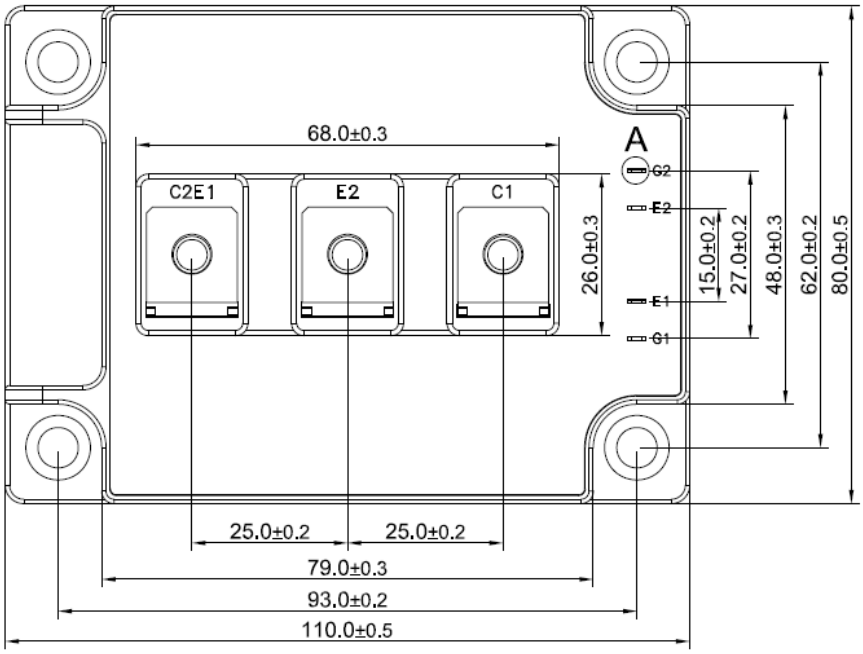
Fig.8 Transient Thermal Impedance (Diode)

Internal Circuit

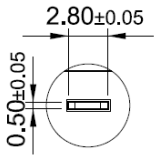


Package Outline (Unit: mm):





View A
scale 3:1



Revision History

Date	Revision	Notes
04/16/2018	01	Initial release

Announcement

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